

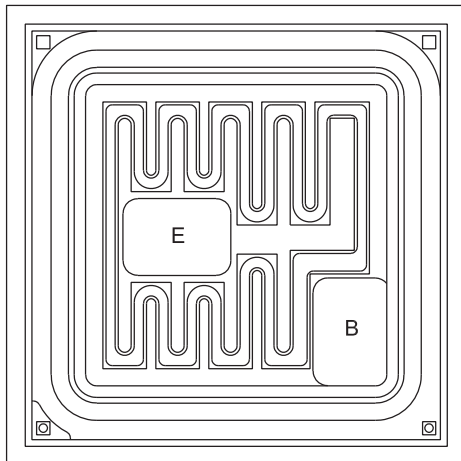
PROCESS CP304V
Small Signal Transistor
NPN - High Current Transistor Chip



PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	22 x 22 MILS
Die Thickness	7.1 MILS
Base Bonding Pad Area	5.7 x 3.9 MILS
Emitter Bonding Pad Area	5.3 x 3.9 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 18,000Å

GEOMETRY



BACKSIDE COLLECTOR R1

GROSS DIE PER 4 INCH WAFER

23,048

PRINCIPAL DEVICE TYPES

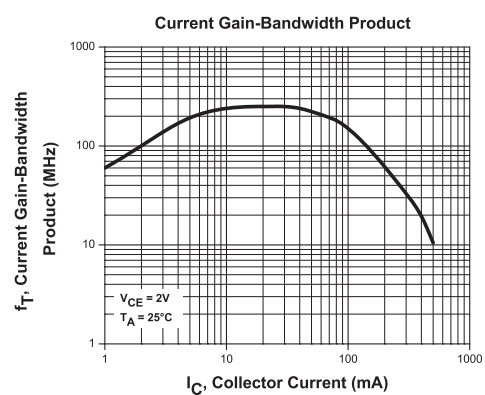
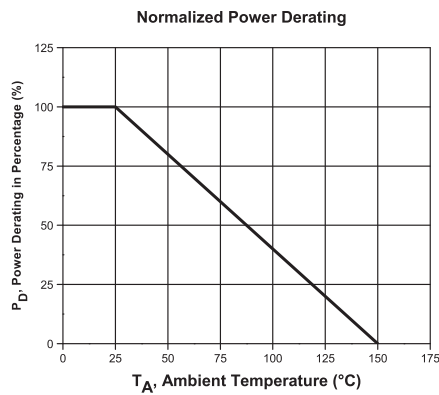
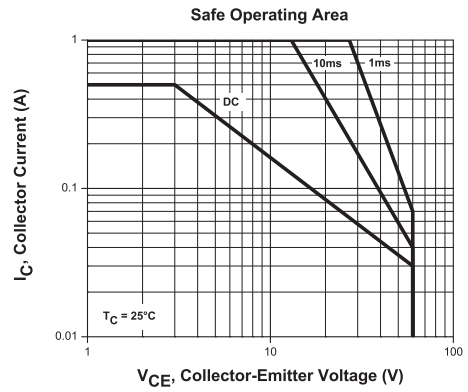
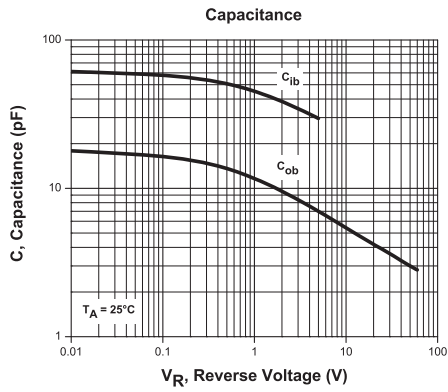
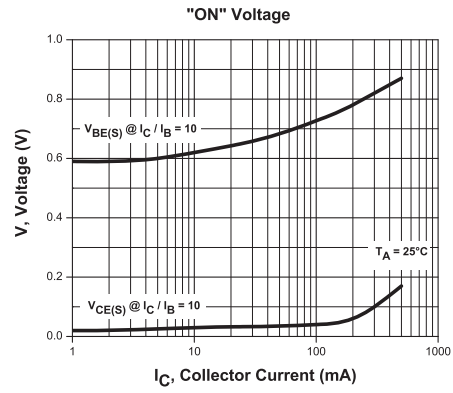
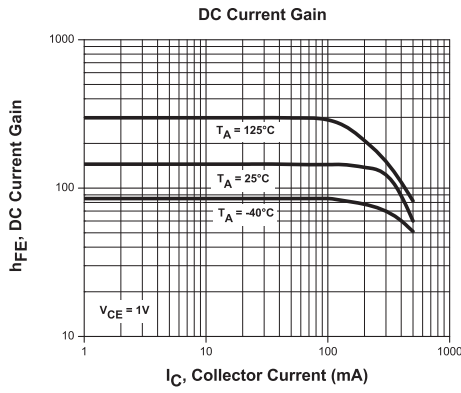
MPSA05

MPSA06

R0 (30-August 2011)

PROCESS CP304V

Typical Electrical Characteristics



R0 (30-August 2011)